

HAT2064R

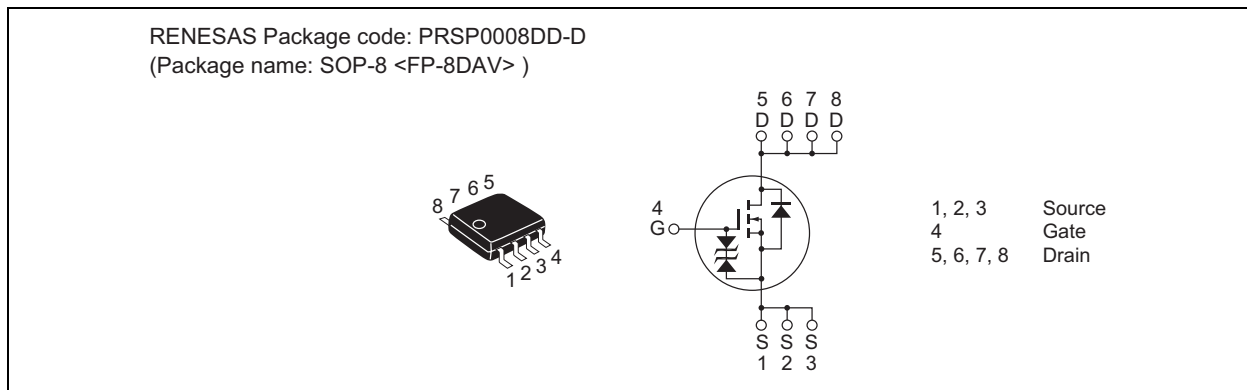
Silicon N Channel Power MOS FET
Power Switching

REJ03G1175-0900
(Previous: ADE-208-930G)
Rev.9.00
Sep 07, 2005

Features

- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
 $R_{DS(on)} = 5.0 \text{ m}\Omega$ typ (at $V_{GS} = 10 \text{ V}$)

Outline



Absolute Maximum Ratings

(T_a = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	16	A
Drain peak current	I _{D (pulse)} ^{Note 1}	128	A
Body-drain diode reverse drain current	I _{DR}	16	A
Channel dissipation	P _{ch} ^{Note 2}	2.5	W
Channel to ambient thermal impedance	θ _{ch-a} ^{Note 2}	50	°C/W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. When using the glass epoxy board (FR4 40 × 40 × 1.6 mm), PW ≤ 10 s

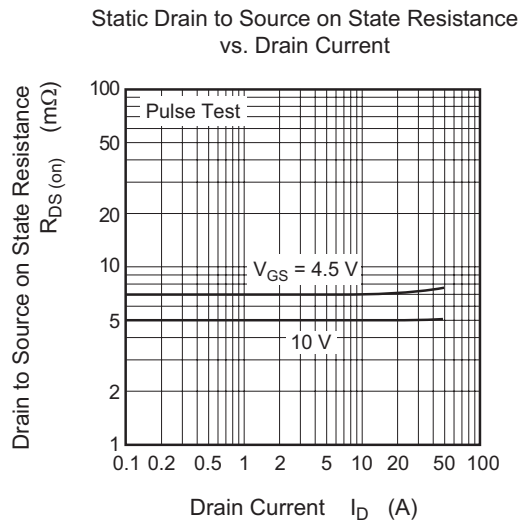
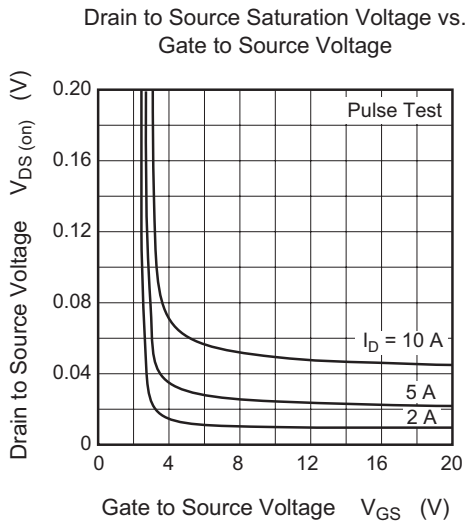
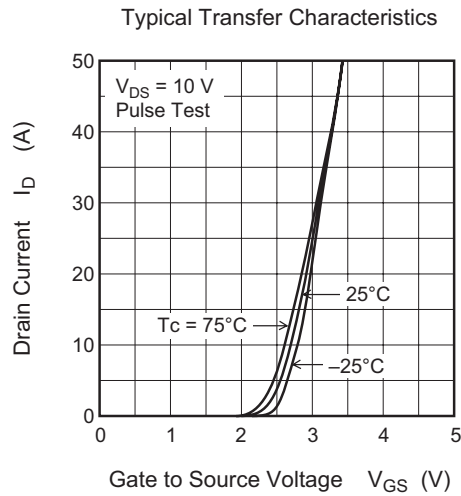
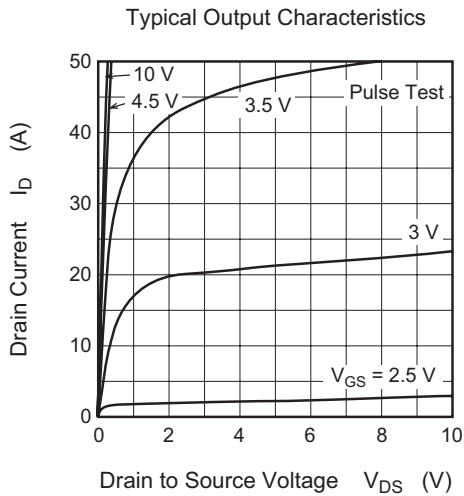
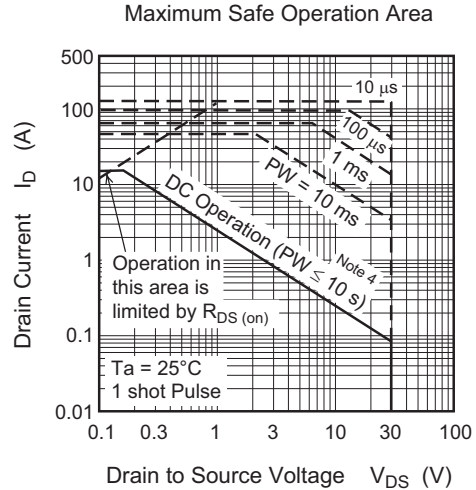
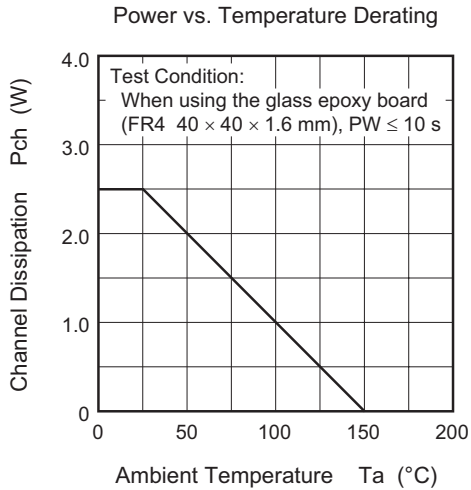
Electrical Characteristics

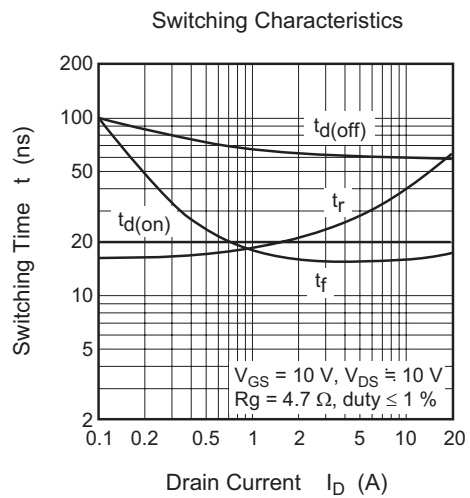
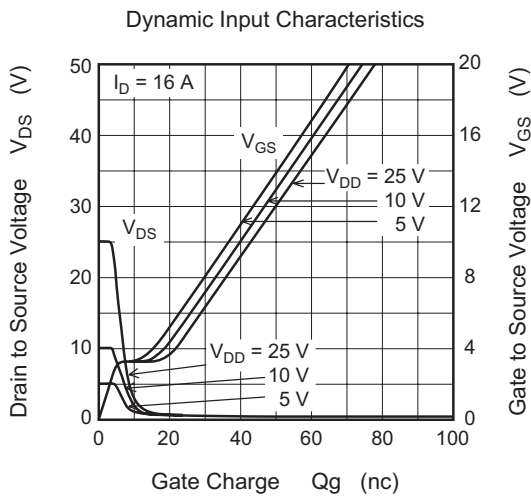
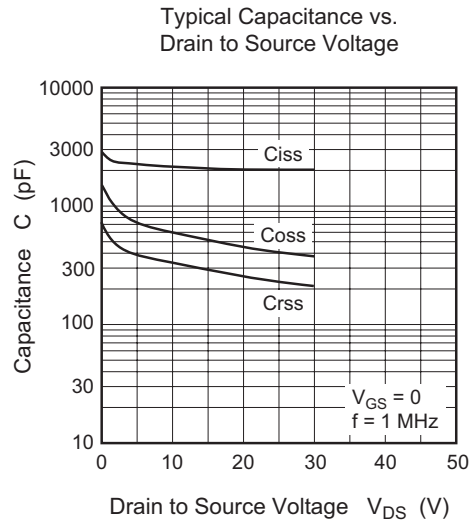
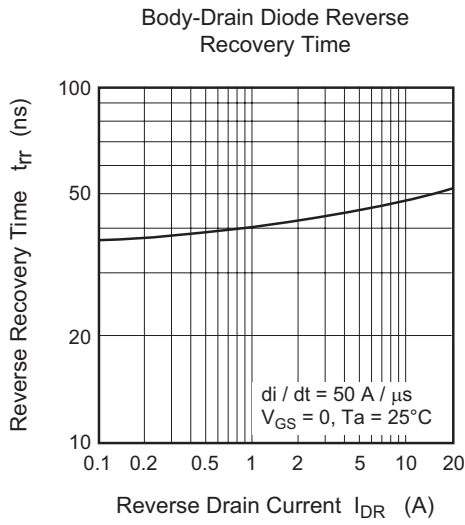
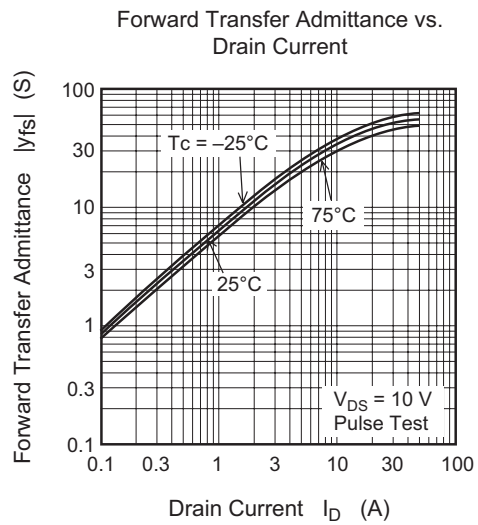
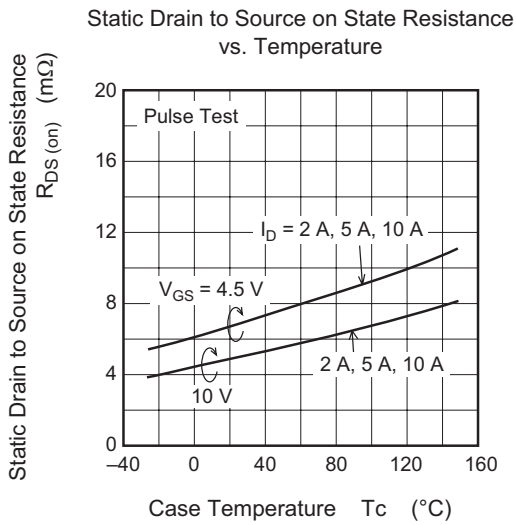
(T_a = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR) DSS}	30	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR) GSS}	±20	—	—	V	I _G = ±100 μA, V _{DS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±16 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	1	μA	V _{DS} = 30 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS (off)}	1.0	—	2.5	V	V _{DS} = 10 V, I _D = 1 mA
Static drain to source on state resistance	R _{DS (on)}	—	5.0	6.3	mΩ	I _D = 8 A, V _{GS} = 10 V ^{Note 3}
	R _{DS (on)}	—	7.0	10	mΩ	I _D = 8 A, V _{GS} = 4.5 V ^{Note 3}
Forward transfer admittance	y _{fs}	18	30	—	S	I _D = 8 A, V _{DS} = 10 V ^{Note 3}
Input capacitance	C _{iss}	—	2200	—	pF	V _{DS} = 10 V
Output capacitance	C _{oss}	—	600	—	pF	V _{GS} = 0
Reverse transfer capacitance	C _{rss}	—	330	—	pF	f = 1 MHz
Total gate charge	Q _g	—	40	—	nC	V _{DD} = 10 V
Gate to source charge	Q _{gs}	—	6	—	nC	V _{GS} = 10 V
Gate to drain charge	Q _{gd}	—	8	—	nC	I _D = 16 A
Turn-on delay time	t _{d (on)}	—	20	—	ns	V _{GS} = 10 V, I _D = 8 A
Rise time	t _r	—	35	—	ns	V _{DD} ≈ 10 V
Turn-off delay time	t _{d (off)}	—	60	—	ns	R _L = 1.25 Ω
Fall time	t _f	—	16	—	ns	R _g = 4.7 Ω
Body-drain diode forward voltage	V _{DF}	—	0.9	1.17	V	I _F = 16 A, V _{GS} = 0 ^{Note 3}
Body-drain diode reverse recovery time	t _{rr}	—	50	—	ns	I _F = 16 A, V _{GS} = 0 di _F /dt = 50 A/μs

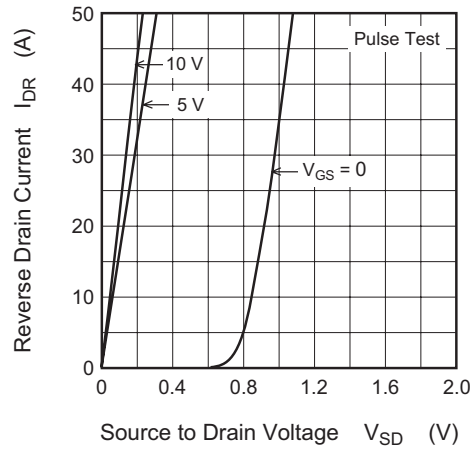
Note: 3. Pulse test

Main Characteristics

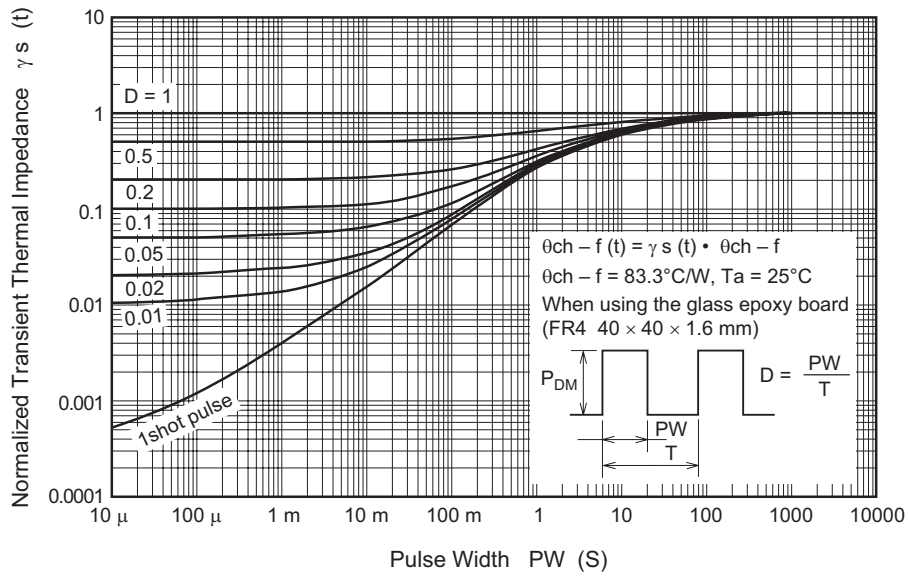




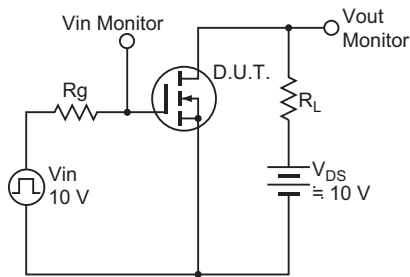
Reverse Drain Current vs. Source to Drain Voltage



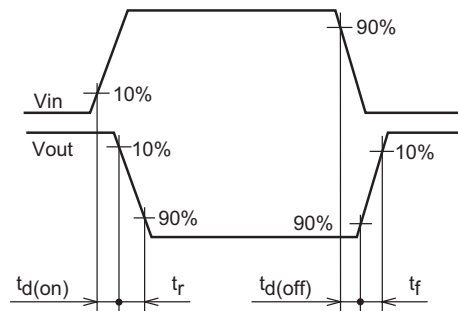
Normalized Transient Thermal Impedance vs. Pulse Width



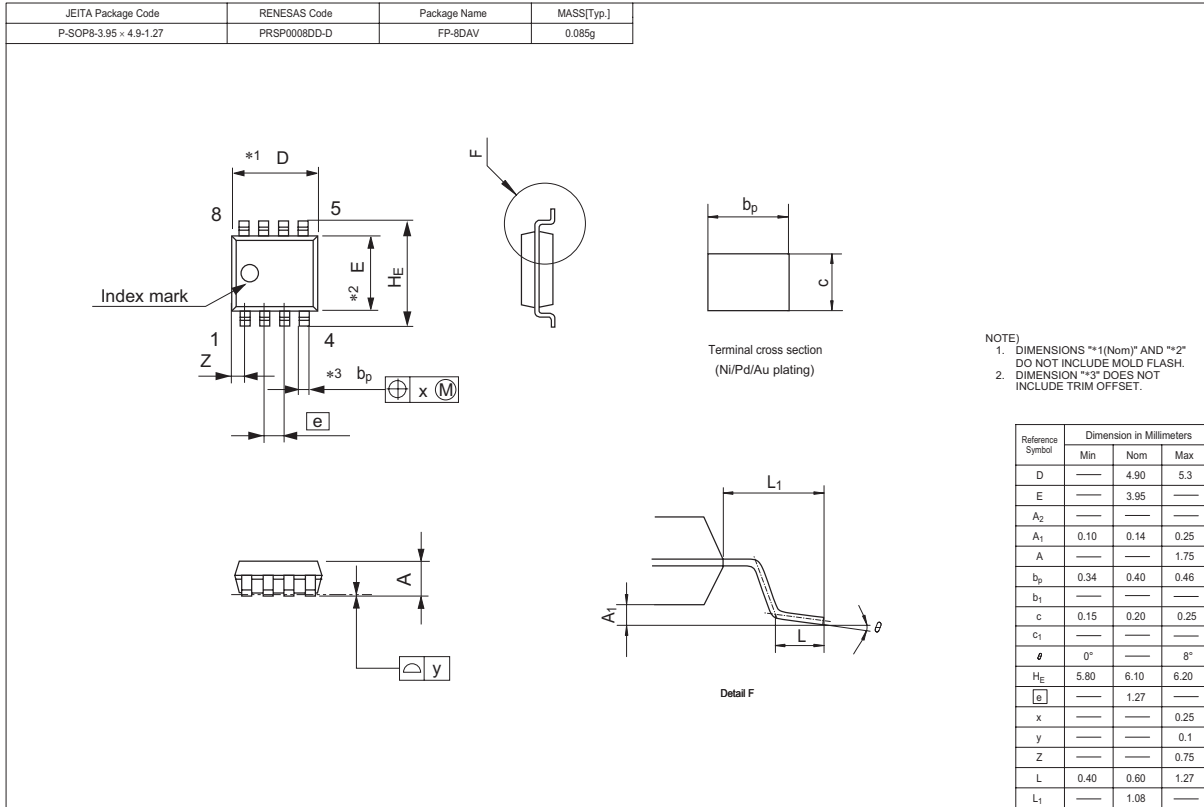
Switching Time Test Circuit



Switching Time Waveform



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT2064R-EL-E	2500 pcs	Taping

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